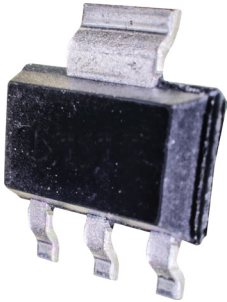


Single Bipolar Transistor multicomp^{PRO}

RoHS
Compliant



Features

- Low saturation voltage

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	100	
Emitter - Base Voltage	V_{EBO}	5	
Peak pulse current	I_{CM}	6	A
Continuous collector current	I_C	2	
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$	120			V
Collector- emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$	100			
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$	5			
Collector cutoff current	I_{CBO}	$V_{CB}=100\text{V},$			0.1	μA
		$V_{CEB}= 100\text{V}, T_{amb} = 100^\circ\text{C}$			10	
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=100\text{mA}^*$		0.13	0.3	V
		$I_C=2\text{A}, I_B=200\text{mA}^*$		0.23	0.5	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{A}, I_B = 100\text{mA}^*$		0.9	1.25	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	$I_C = 1\text{A } V_{CE}=2\text{V}^*$		0.8	1	
Static Forward Current Transfer Ratio	h_{FE}	$I_C = 50\text{mA}, V_{CE} = 2\text{V}^*$	70	200		
		$I_C = 500\text{mA}, V_{CE} = 2\text{V}^*$	100	200	300	
		$I_C = 1\text{A}, V_{CE} = 2\text{V}^*$	55	110		
		$I_C = 2\text{A } V_{CE} = 2\text{V}^*$	25	55		
Transitional frequency	f_T	$I_C=10\text{mA}, V_{CE}= 5\text{V}, f=100\text{MHz}$	140	175		MHz
Output capacitance	C_{obo}	$V_{CB}= 10\text{V}, f=1\text{MHz}$			30	pF
Switching times	t_{on}	$I_C=500\text{mA}, V_{CC}=10\text{V}, I_{B1}=I_{B2}=50\text{mA}$		80		nS
	t_{off}			1200		

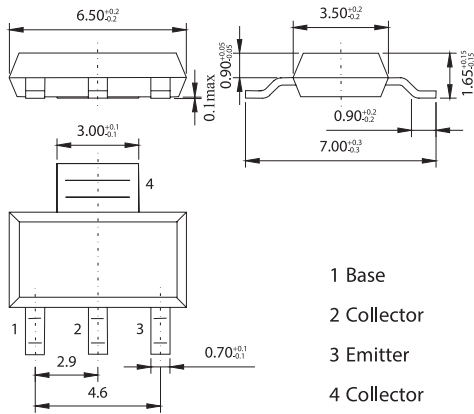
Measured under pulsed conditions. Pulse Width=300 μs . Duty cycles ≤ 2

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Single Bipolar Transistor multicomp^{PRO}

Diagram



- 1 Base
- 2 Collector
- 3 Emitter
- 4 Collector

Part Number Table

Description	Part Number
Single Bipolar Transistor, NPN, 2A, 100V, SOT 223	FZT653

Dimensions : Millimetres

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